2SC4617

NPN Silicon General Purpose Amplifier Transistor

This NPN transistor is designed for general purpose amplifier applications. This device is housed in the SC−75/SOT-416 package which is designed for low power surface mount applications, where board space is at a premium.

Features

- Pb−Free Package is Available*
- Reduces Board Space
- High h_{FE}, 210−460 (typical)
- Low $V_{CE(sat)}$, < 0.5 V
- Available in 8 mm, 7 inch/3000 Unit Tape and Reel

*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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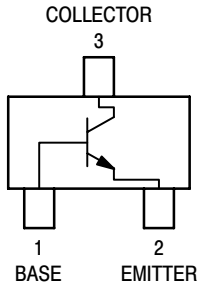
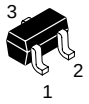
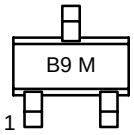
NPN GENERAL PURPOSE AMPLIFIER TRANSISTORS SURFACE MOUNT





SC−75
CASE 463
STYLE 1

MARKING DIAGRAM



B9 = Specific Device Code
M = Date Code

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C)

Rating	Symbol	Value	Unit
Collector-Base Voltage	$V_{(BR)CBO}$	50	Vdc
Collector-Emitter Voltage	$V_{(BR)CEO}$	50	Vdc
Emitter-Base Voltage	$V_{(BR)EBO}$	5.0	Vdc
Collector Current − Continuous	I_C	100	mAdc

Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Power Dissipation (Note 1)	P_D	125	mW
Junction Temperature	T_J	150	°C
Storage Temperature Range	T_{stg}	−55 ~ +150	°C

1. Device mounted on a FR-4 glass epoxy printed circuit board using the minimum recommended footprint.

ELECTRICAL CHARACTERISTICS (T_A = 25°C)

Characteristic	Symbol	Min	Typ	Max	Unit
Collector-Base Breakdown Voltage (I_C = 50 μAdc, I_E = 0)	$V_{(BR)CBO}$	50	−	−	Vdc
Collector-Emitter Breakdown Voltage (I_C = 1.0 mAdc, I_B = 0)	$V_{(BR)CEO}$	50	−	−	Vdc
Emitter-Base Breakdown Voltage (I_E = 50 μAdc, I_E = 0)	$V_{(BR)EBO}$	5.0	−	−	Vdc
Collector-Base Cutoff Current (V_{CB} = 30 Vdc, I_E = 0)	I_{CBO}	−	−	0.5	μA
Emitter-Base Cutoff Current (V_{EB} = 4.0 Vdc, I_B = 0)	I_{EBO}	−	−	0.5	μA
Collector-Emitter Saturation Voltage (Note 2) (I_C = 60 mAdc, I_B = 5.0 mAdc)	$V_{CE(sat)}$	−	−	0.4	Vdc
DC Current Gain (Note 2) (V_{CE} = 6.0 Vdc, I_C = 1.0 mAdc)	h_{FE}	120	−	560	−
Transition Frequency (V_{CE} = 12 Vdc, I_C = 2.0 mAdc, f = 30 MHz)	f_T	−	180	−	MHz
Output Capacitance (V_{CB} = 12 Vdc, I_C = 0 Adc, f = 1 MHz)	C_{OB}	−	2.0	−	pF

2. Pulse Test: Pulse Width ≤ 300 μs, D.C. ≤ 2%.

ORDERING INFORMATION

Device	Package	Shipping†
2SC4617	SC−75	3,000 / Tape & Reel
2SC4617G	SC−75 (Pb−Free)	3,000 / Tape & Reel
2SC4617T1	SC−75	3,000 / Tape & Reel
2SC4617T1G	SC−75 (Pb−Free)	3,000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL ELECTRICAL CHARACTERISTICS

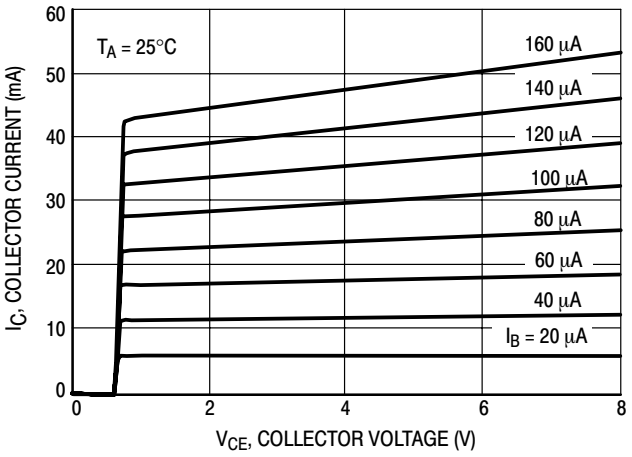


Figure 1. $I_C - V_{CE}$

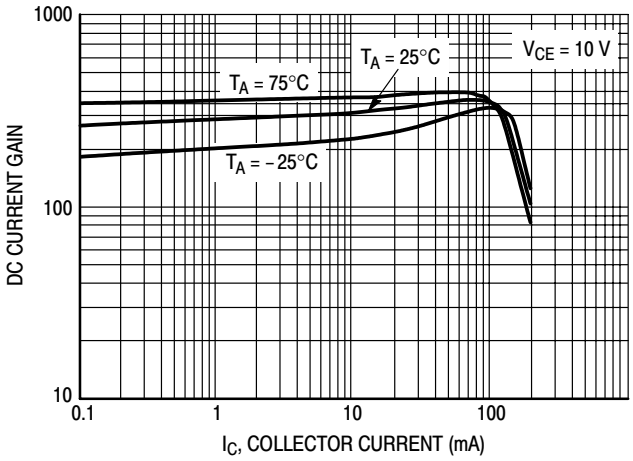


Figure 2. DC Current Gain

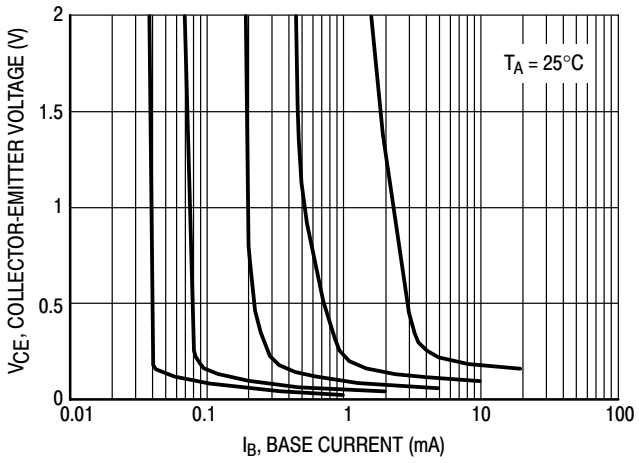


Figure 3. Collector Saturation Region

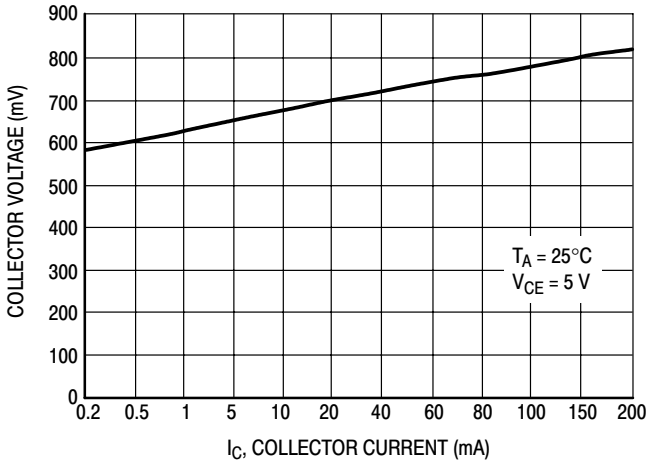


Figure 4. On Voltage

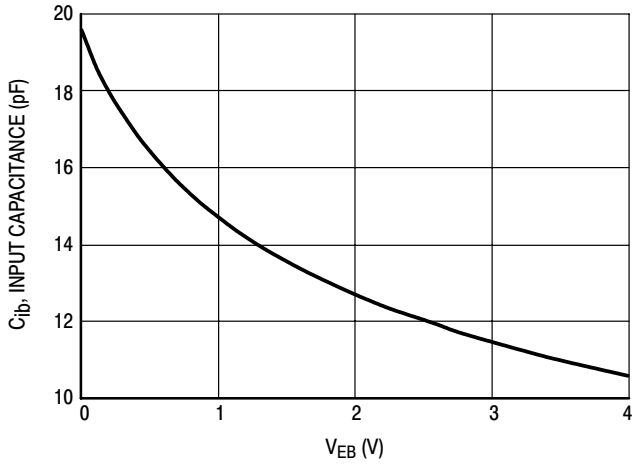


Figure 5. Capacitance

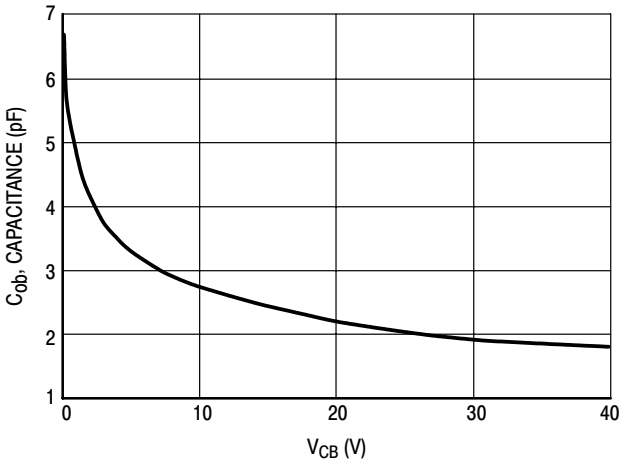
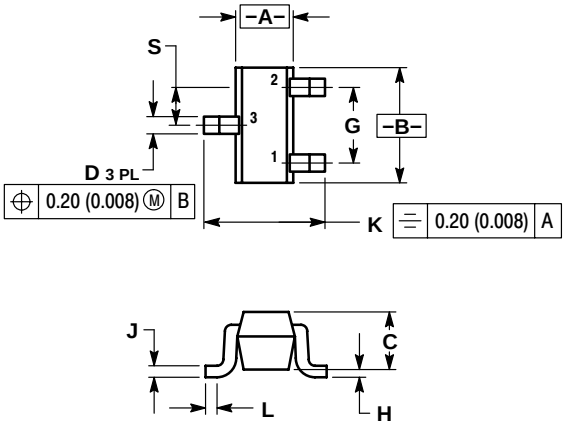


Figure 6. Capacitance

2SC4617

PACKAGE DIMENSIONS

SC−75 (SOT−416)
CASE 463−01
ISSUE C



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETER.

	MILLIMETERS		INCHES	
DIM	MIN	MAX	MIN	MAX
A	0.70	0.90	0.028	0.035
B	1.40	1.80	0.055	0.071
C	0.60	0.90	0.024	0.035
D	0.15	0.30	0.006	0.012
G	1.00 BSC		0.039 BSC	
H	−−−	0.10	−−−	0.004
J	0.10	0.25	0.004	0.010
K	1.45	1.75	0.057	0.069
L	0.10	0.20	0.004	0.008
S	0.50 BSC		0.020 BSC	

STYLE 1:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT:
Literature Distribution Center for ON Semiconductor
P.O. Box 61312, Phoenix, Arizona 85082−1312 USA
Phone: 480−829−7710 or 800−344−3860 Toll Free USA/Canada
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Japan: ON Semiconductor, Japan Customer Focus Center
2−9−1 Kamimeguro, Meguro−ku, Tokyo, Japan 153−0051
Phone: 81−3−5773−3850

ON Semiconductor Website: http://onsemi.com

Order Literature: http://www.onsemi.com/litorder

For additional information, please contact your local Sales Representative.

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